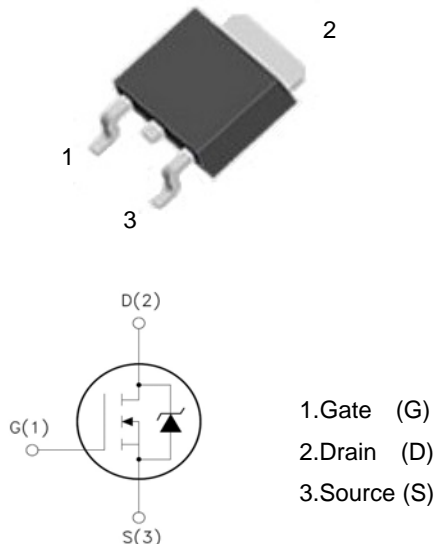


## XXW9N20

### Features

- Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Extended Safe Operating Area
- Unrivalled Gate Charge : 22 nC (Typ.)
- BVDSS=200V, ID=9A
- Lower  $R_{DS(on)}$  : 0.4  $\Omega$  (Max) @VG=10V
- 100% Avalanche Tested

TO-252



### Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain-Source Voltage	200	V
$I_D$	Drain Current	$T_j=25^\circ\text{C}$	9.0
		$T_j=100^\circ\text{C}$	5.7
$V_{GS(TH)}$	Gate Threshold Voltage	$\pm 30$	V
$E_{AS}$	Single Pulse Avalanche Energy (note1)	160	mJ
$I_{AR}$	Avalanche Current (note2)	9.0	A
$P_D$	Power Dissipation ( $T_j=25^\circ\text{C}$ )	72	W
$T_j$	Junction Temperature(Max)	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^\circ\text{C}$
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

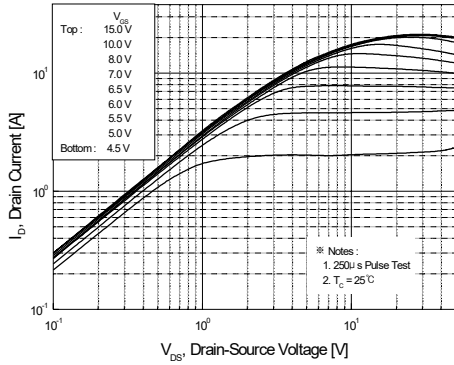
### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	-	1.74	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	$^\circ\text{C}/\text{W}$

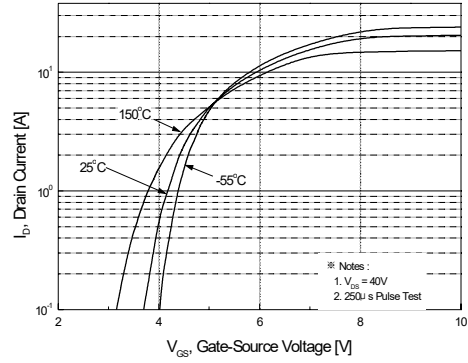
**Electrical Characteristics** (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	ID=250 μ A, VGS=0	200	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	ID=250 μ A, Reference to 25°C	--	0.55	--	V/°C
IDSS	Zero Gate Voltage Drain Current	Vds=200V, Vgs=0V	--	--	1	μ A
		Vds=160V, Tc=125°C			10	μ A
IGSSF	Gate-body leakage Current, Forward	Vgs=+30V, Vds=0V	--	--	100	nA
IGSSR	Gate-body leakage Current, Reverse	Vgs=-30V, Vds=0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	Id=250uA, Vds=Vgs	2	--	4	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	Id=4.5A, Vgs=10V	--	--	0.4	Ω
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=25V, VGS=0, f=1.0MHz	--	550	720	pF
Coss	Output Capacitance		--	85	110	pF
Crss	Reverse Transfer Capacitance		--	22	29	pF
<b>Switching Characteristics</b>						
Td(on)	Turn-On Delay Time	VDD=100V, ID=9A, RG=25 Ω (Note 3,4)	--	11	25	nS
Tr	Turn-On Rise Time		--	70	140	nS
Td(off)	Turn-Off Delay Time		--	60	120	nS
Tf	Turn-Off Fall Time		--	65	130	nS
Qg	Total Gate Charge	VDS=160, VGS=10V, ID=9A (Note 3,4)	--	22	30	nC
Qgs	Gate-Source Charge		--	4	--	nC
Qgd	Gate-Drain Charge		11	--	nC	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
IS	Maximum Continuous Drain-Source Diode Forward Current		--	--	9	A
ISM	Maximum Pulsed Drain-Source Diode Forward Current		--	--	36	A
VSD	Drain-Source Diode Forward Voltage	Id=9A	--	--	1.45	V
trr	Reverse Recovery Time	IS=9.0A, VGS=0V	--	140	--	nS
Qrr	Reverse Recovery Charge	di/dt=100A/μ S (Note3)	--	2.2	--	μ C
*Notes	1, L=8mH, IAS=9A, VDD=50V, RG=25Ω, Starting TJ =25°C 2, Repetitive Rating : Pulse width limited by maximum junction temperature 3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2% 4, Essentially Independent of Operating Temperature					

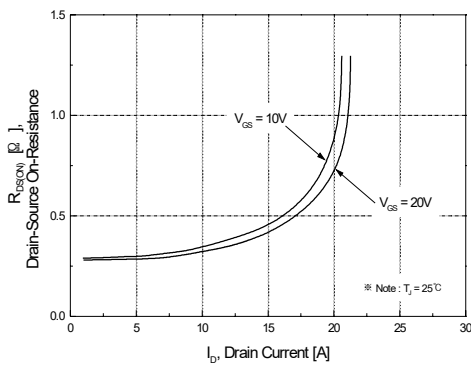
**Typical Characteristics**



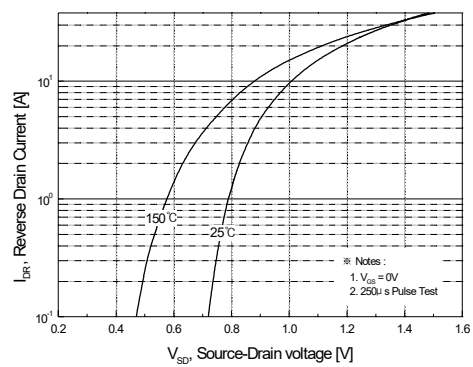
**Figure 1. On-Region Characteristics**



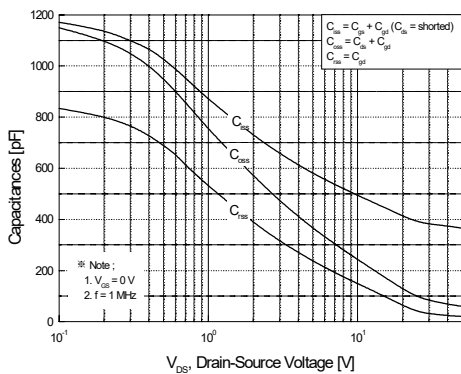
**Figure 2. Transfer Characteristics**



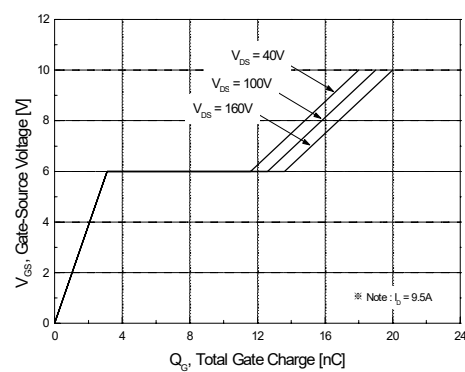
**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

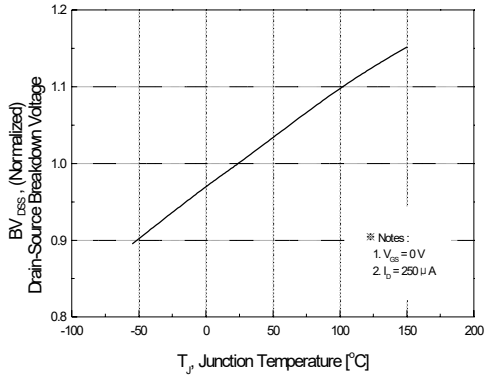


**Figure 5. Capacitance Characteristics**

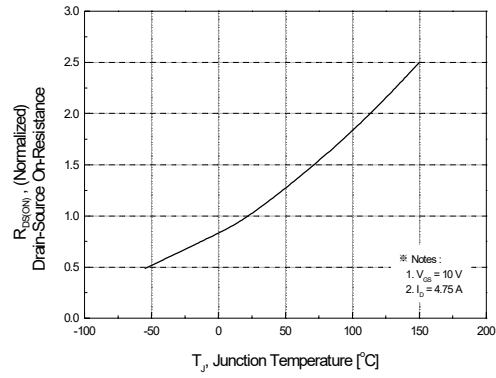


**Figure 6. Gate Charge Characteristics**

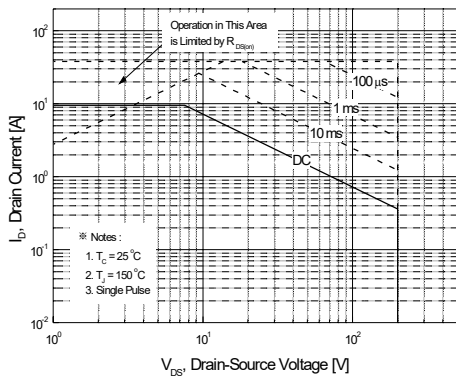
**Typical Characteristics (Continued)**



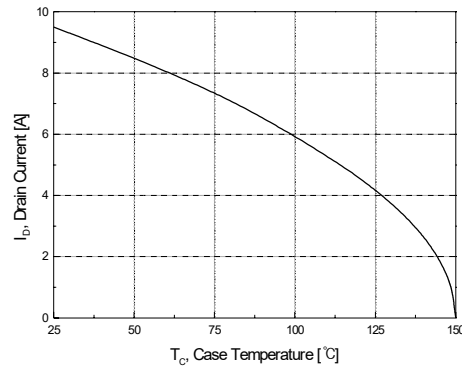
**Figure 7. Breakdown Voltage Variation vs Temperature**



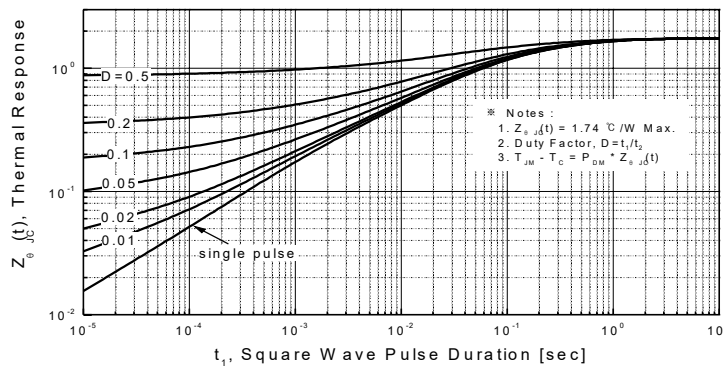
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for WGP9N20**

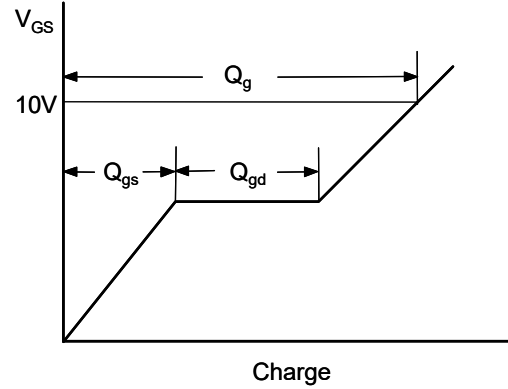
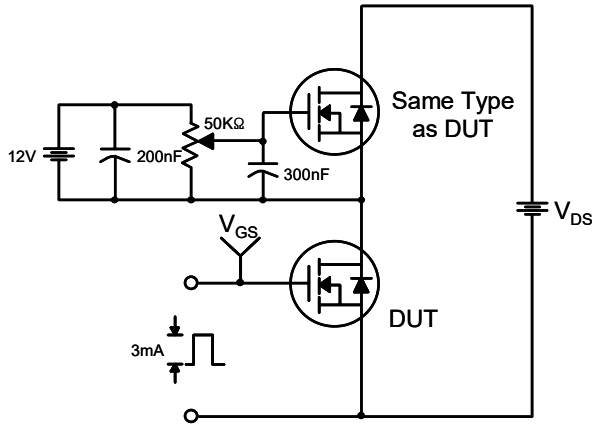


**Figure 10. Maximum Drain Current vs Case Temperature**

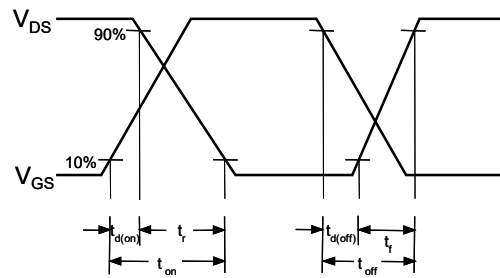
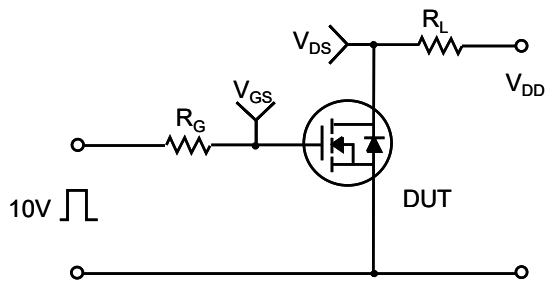


**Figure 11-1. Transient Thermal Response Curve for WGP9N20**

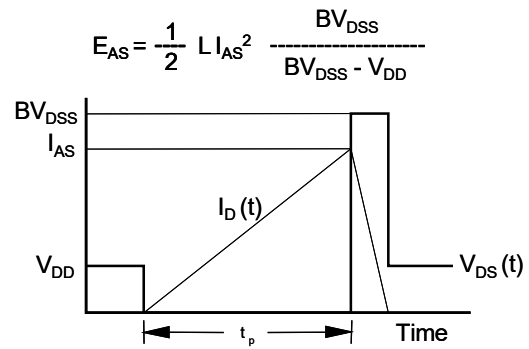
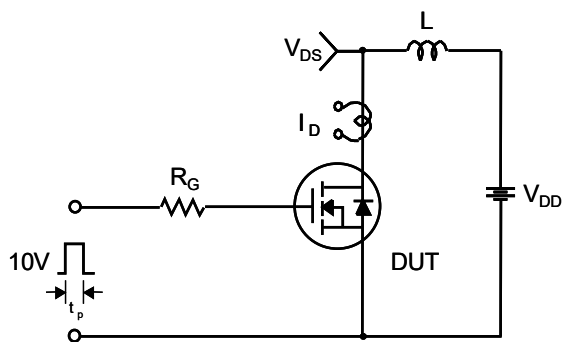
**Gate Charge Test Circuit & Waveform**



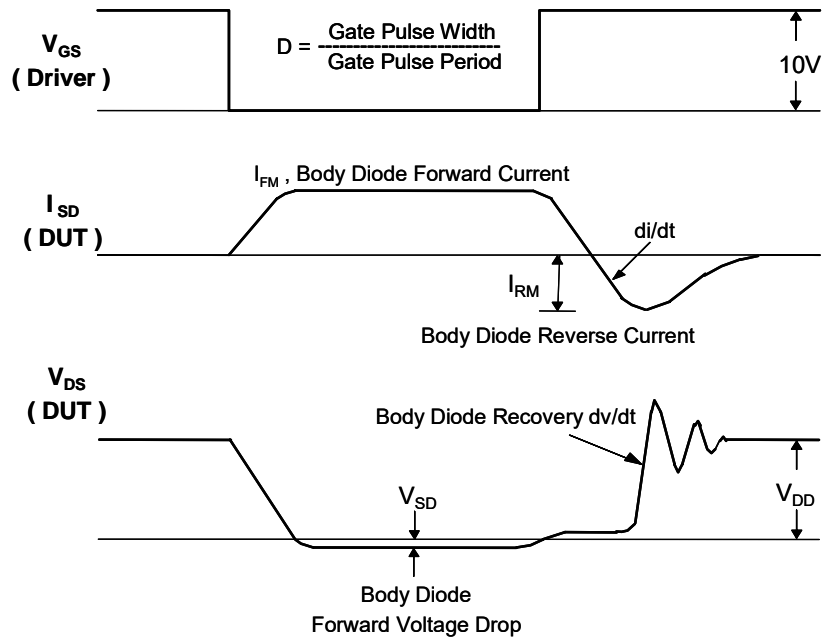
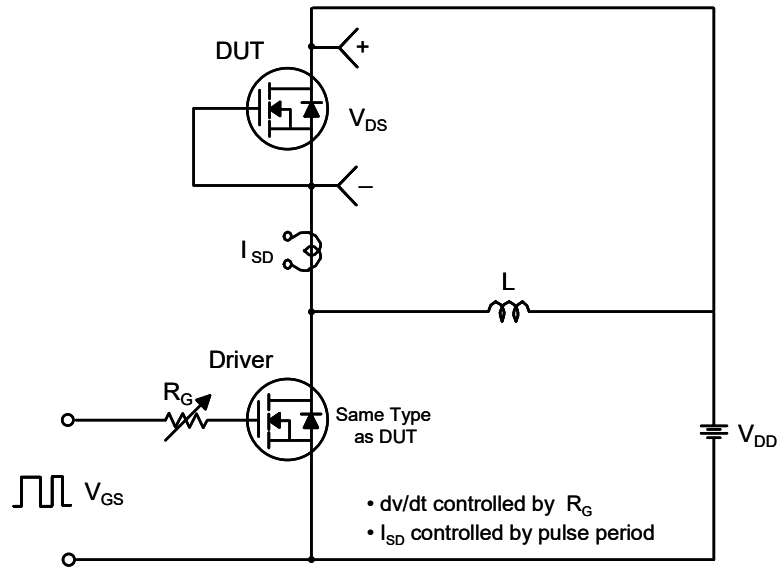
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-252

Unit: mm

